1201,63407

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Nayfeh et al.)	I hereby certify that this paper is being deposited with the United States Postal Service as FIRST-CLASS mail		
Serial No.:	09/496,506)	in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this date.		
Filed:	February 2, 2000)	Date Registration No. 43,814 F-CLASS, WCM		
For:	SILICON NANOPARTICLE FIELD EFFECT TRANSISTOR AND TRANSISTOR MEMORY DEVICE))))	Appr. February 20, 1998 App. February 20, 1998 Appr. February 20, 1998 App. February 20, 1998 Ap		
Art Unit:	1741)	(C) FJONES 5-15-0		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, applicants through counsel

herewith:

Submit a copy of the publication set forth in the attached form PTO-1449 as

follows:

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REMARKS

Applicants respectfully request that the Examiner consider the above-listed references in the examination of this application and list these references of record in the application.

Respectfully submitted,

GREER, BURNS & CRAIN, LTD.

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